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## EI/IC-403 (New)

## **B.E. IV Semester**

Examination, June 2016

## **Electronic Devices**

Time: Three Hours

Maximum Marks: 70

**Note:** i) Answer five questions. In each question part A, B, C is compulsory and D part has internal choice.

- ii) All parts of each question are to be attempted at one place.
- iii) All questions carry equal marks, out of which part A and B (Max. 50 words) carry 2 marks, part C (Max. 100 words) carry 3 marks, part D (Max. 400 words) carry 7 marks.
- iv) Except numericals, Derivation, Design and Drawing etc.
- v) Assume suitable data if any missing.
- a) Explain Intrinsic and Extrinsic Semiconductor.
  - b) What do you mean by drift and diffusion current?
  - c) Discuss Hall effect and its applications.
  - d) Draw and explain the VI characteristics of a PN junction diode.

OR

Derive the expression for transition and diffusion capacitance.

- a) Explain avalanche breakdown.
  - b) Explain PIN diode.
  - c) Explain diode as a rectifier.
  - d) Discuss Zener Diode and how it is used as a voltage regulator.

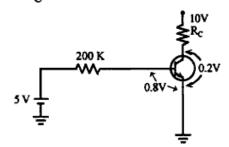
OR

Explain two level clipper with example.

- 3. a) Explain transistor as switch.
  - b) Explain current amplification factor.
  - c) Compare the three configuration of the transistor in minimum five points.
  - Explain CB configuration and draw the Input/Output characteristics of CB configuration.

OR

A silicon transistors with  $V_{BE, sat} = 0.8 \text{ V}$ ,  $h_{fe} = 100$ ,  $V_{CE,sat} = 0.2 \text{ V}$  in the circuit shown. Find the minimum value of  $R_C$  for which transistors remains in saturation.



- 4. a) Explain the DC load line in detail.
  - b) Give the name of the techniques used for Bias compensation.
  - c) Explain fixed bias circuit in detail.
  - d) Explain Transistor as an amplifier in detail.

OR

Explain the Diode Compensation Technique.

- 5. a) Give the difference between BJT and FET. (any three)
  - b) Explain Drain, Source and Gate of FET.
  - Give the relation between r<sub>d</sub>, g<sub>m</sub> and μ.
  - Explain the construction and operation of enhancement type MOSFET with diagram.

OR

Explain FET as a:

- i) Voltage variable Resistor
- ii) An amplifier

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